

marked up version of each amended claim. Applicant also lists all pending claims remaining in the present application as follows:

SUB  
E<sub>1</sub>

1. A method of etching a metallic film, comprising the steps of:  
forming a metallic film on a thin film resistor;  
forming a conductive film on the metallic film;  
forming a first opening in the conductive film to expose the metallic film from the first opening;  
forming a mask on the conductive film, the mask having a second opening having an opening area smaller than that of the first opening and open in the first opening to expose the metallic film therefrom; and  
etching the metallic film through the second opening.
2. The method of Claim 1, wherein the step of etching the metallic film includes steps of:  
dry-etching a first part of the metallic film through the second opening; and  
wet-etching a second part of the metallic film, the second part directly contacting the thin film resistor.
3. The method of Claim 1, wherein a side wall of the first opening is entirely covered with the mask defining the second opening therein.

4. The method of Claim 1, wherein the step of forming the mask includes steps of:

forming a photo-resist on the conductive film and in the first opening to serve as the mask; and

removing a part of the photo-resist to form the second opening.

7. (Amended) The method of Claim 2, wherein a thickness of the first part is equal to or larger than 20% relative to an entire thickness of the metallic film.

8. (Amended) The method of Claim 2, wherein a thickness of the second part is equal to or larger than 100 Å.

9. (Amended) The method of Claim 2, wherein the step of dry-etching the metallic film uses an etching gas including  $\text{CF}_4$ .

10. (Amended) The method of Claim 2, wherein the step of wet-etching the metallic film uses an etching solution including  $\text{H}_2\text{O}_2$ .

11. (Amended) The method of Claim 2, wherein the metallic film is formed with a thickness equal to or larger than 500 Å.

26. (Amended) The method of Claim 2, wherein the metallic film is a single layer.